



#### **70V N-CHANNEL ENHANCEMENT MODE MOSFET**

# **Product Summary**

ſ	V <sub>(BR)DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C	
I	70V	0.13Ω @ V <sub>GS</sub> = 10V	3.8A	

## Description

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage power management applications.

# Applications

- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control
- Class D Audio Output Stages

# **Features and Benefits**

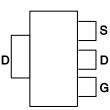
- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## **Mechanical Data**

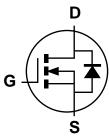
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)



Top View



Pin Out - Top View





# Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
ZXMN7A11GTA	Standard	SOT223	1,000 / Tape & Reel
ZXMN7A11GTC	Standard	SOT223	4,000 / Tape & Reel

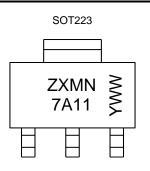
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



ZXMN 7A11 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{WW}$  = Week Code (01~53)



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V <sub>DSS</sub>	70	V	
Gate-Source Voltage	V <sub>G</sub>	±20	V	
Continuous Drain Current, V <sub>GS</sub> = 10V,	$T_A = +25^{\circ}C$ (Note 6) $T_A = +70^{\circ}C$ (Note 6) $T_A = +25^{\circ}C$ (Note 5)	I <sub>D</sub>	3.8 3.0 2.7	A
Maximum Continuous Body Diode Forward Current (Note 6)	Is	5	А	
Pulsed Drain Current	I <sub>DM</sub>	10	А	
Pulsed Source Current (Body Diode)	I <sub>SM</sub>	10	А	

## Thermal Resistance (@T<sub>A</sub> = +25°C, unless otherwise specified.)

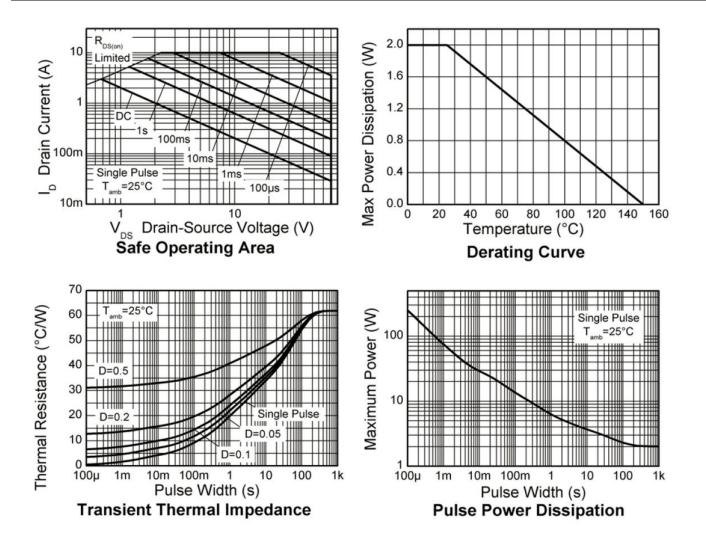
Symbol	Value	Units
	2.0	W
PD	16	mW/°C
PD	3.9 31	W mW/°C
R <sub>0JA</sub>	62.5	°C/W
R <sub>0JA</sub>	32	°C/W
T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C
-	P <sub>D</sub> P <sub>D</sub> R <sub>θJA</sub> R <sub>θJA</sub>	$ \begin{array}{c}     P_{D} & \frac{2.0}{16} \\     P_{D} & \frac{3.9}{31} \\     R_{\theta JA} & 62.5 \\     R_{\theta JA} & 32 \end{array} $

5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions. 6. For a device surface mounted on FR4 PCB measured at t  $\leq$  5 sec.

7. Repetitive rating 25mm x 25mm FR4 PCB, D=0.05 pulse width=10µs - pulse width limited by maximum junction temperature.



# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)





# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

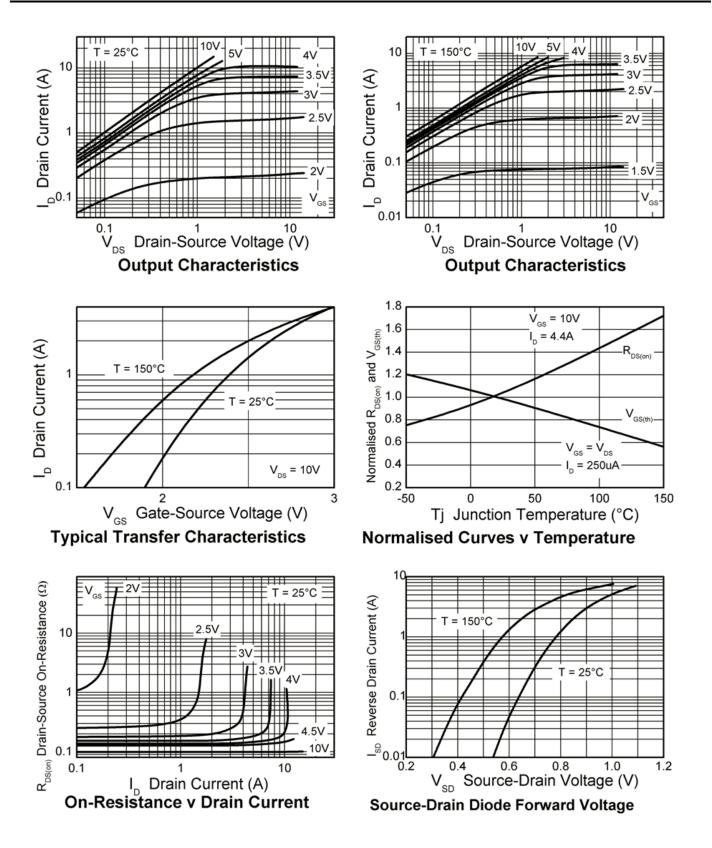
Ob and a tank the	Ourseland	N#!	<b>T</b>	Maria	1114	To al Open dition	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	70	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	$V_{DS} = 70V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	—	—	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Statia Drain Source On Begistenes (Note 9)	Deserve	—	—	0.13	Ω	$V_{GS} = 10V, I_D = 4.4A$	
Static Drain-Source On-Resistance (Note 8)	R <sub>DS</sub> (ON)	—	—	0.19	Ω	$V_{GS} = 4.5V, I_D = 3.8A$	
Forward Transfer Admittance	<b>g</b> fs	_	4.66	_	S	$V_{DS} = 15V, I_D = 4.4A$	
Diode Forward Voltage (Note 8)	V <sub>SD</sub>	—	0.85	0.95	V	$T_J$ = +25°C , $V_{GS}$ = 0V, $I_S$ = 2.5A	
DYNAMIC CHARACTERISTICS (Notes 9 &10)							
Input Capacitance	Ciss	—	298	_	pF	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V f = 1.0MHz	
Output Capacitance	Coss	—	35	_			
Reverse Transfer Capacitance	Crss	—	21	_			
Total Gate Charge	Qg	_	4.35		nC	$V_{DS} = 35V, V_{GS} = 5.0V, I_D = 4.4A$	
Total Gate Charge	Qg	_	7.4	—		$V_{DS} = 35V, V_{GS} = 10V, I_D = 4.4A$	
Gate-Source Charge	Q <sub>gs</sub>	_	1.06	—	nC		
Gate-Drain Charge	Q <sub>gd</sub>	_	1.8	_			
Turn-On Delay Time	t <sub>D(on)</sub>	_	1.9	—			
Turn-On Rise Time	tr		2	_		$\label{eq:VDS} \begin{split} V_{DS} &= 35V, \ V_{GS} = 10V, \\ I_D &= 1 \ A, \ R_G \cong 6.0\Omega \end{split}$	
Turn-Off Delay Time	t <sub>D(off)</sub>		11.5	_	ns		
Turn-Off Fall Time	t <sub>f</sub>		5.8	—	1		
Body Diode Reverse Recovery Time	t <sub>rr</sub>	_	19.8		ns	T <sub>J</sub> = +25°C, IS = 2.5A,	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	_	14		nC	dl/dt = 100A/µs	

Notes:

Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperature.
 For design aid only, not subject to production testing.

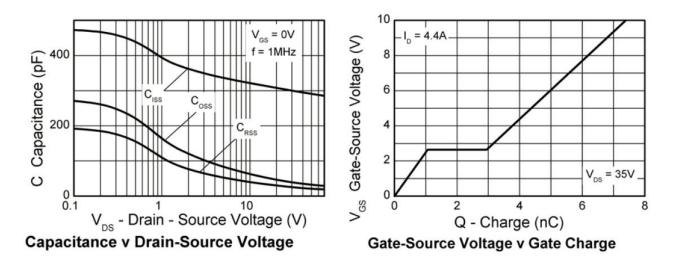


# **Typical Characteristics**



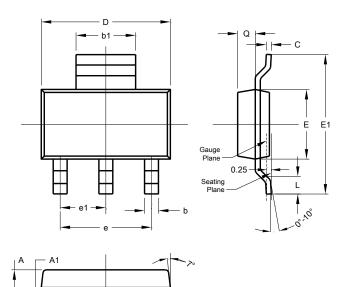


# **Typical Characteristics**





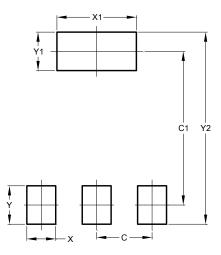
Package Outline Dimensions Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All [	All Dimensions in mm				

# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



<b>D</b> : .	
Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



#### IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

#### LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2015, Diodes Incorporated

#### www.diodes.com

单击下面可查看定价,库存,交付和生命周期等信息

>>Diodes Incorporated(达迩科技(美台))